

UV385S1N1

Features

Indium Gallium nitride based material
Broad band UVA+UVB+UVC photodiode
Photovoltaic mode operation
TO-46 metal housing
High responsivity and low dark current

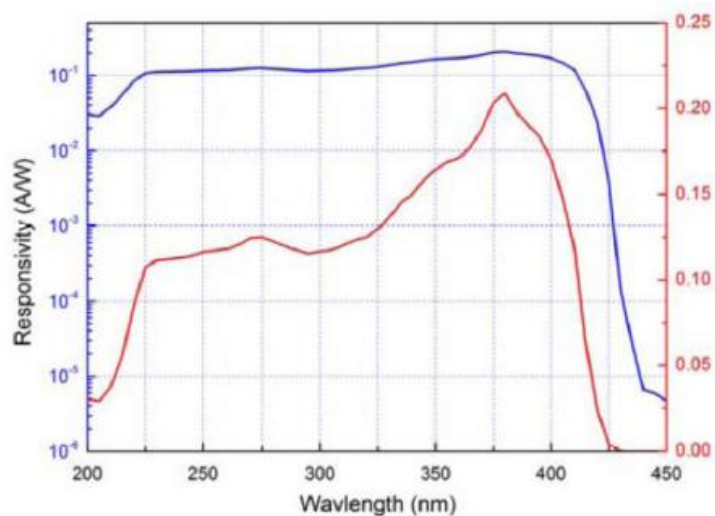
Applications

UV LED monitoring
UV radiation dose measurement
UV Curing

Specifications

Parameter	Symbol	Value	Unit
Wavelength of peak responsivity	λ_{max}	385	nm
Peak responsivity (at 385nm)	Rmax	0.205	A/W
Spectral response range		220~420	nm
UV/visible rejection ratio (Rmax/R400 nm)	VB	$>10^3$	
Chip size	A	1	mm ²
Dark current (1 V reverse bias)	I _d	<1	nA
Capacitance (at 0 V and 1 MHz)	C	55	pF
Temperature coefficient	T _c	-0.1	%/°C
Operation temperature range	T _{opt}	-10~60	°C
Storage temperature range	T _{stor}	-40~85	°C
Soldering temperature (3 s)	T _{sold}	260	°C
Reverse voltage	V _{Rmax}	10	V

Spectral response



Package dimensions

